

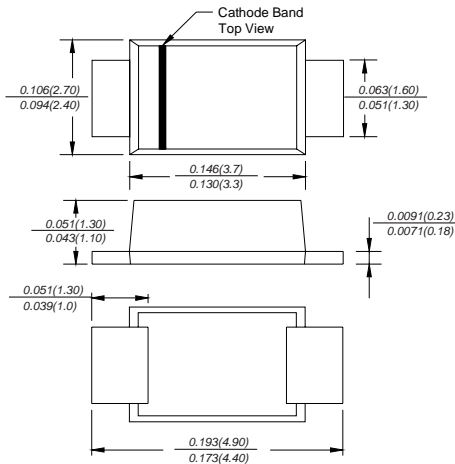


SS32F THRU SS3200F

SURFACE MOUNT SCHOTTKY BARRIER RECTIFIER

Reverse Voltage - 20 to 200 Volts Forward Current - 3.0 Ampere

SMAF



Dimensions in inches and (millimeters)

FEATURES

- ◆ The plastic package carries Underwriters Laboratory Flammability Classification 94V-0
- ◆ For surface mounted applications
- ◆ Metal silicon junction, majority carrier conduction
- ◆ Low power loss, high efficiency
- ◆ Built-in strain relief, ideal for automated placement
- ◆ High forward surge current capability
- ◆ High temperature soldering guaranteed: 260°C/10 seconds at terminals

MECHANICAL DATA

Case: JEDEC SMAF molded plastic body
Terminals: leads solderable per MIL-STD-750, Method 2026
Polarity: Color band denotes cathode end
Mounting Position: Any
Weight: 0.0018 ounce, 0.064 grams

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25°C ambient temperature unless otherwise specified.
 Single phase half-wave 60Hz, resistive or inductive load, for capacitive load current derate by 20%.

MDD Catalog Number	SYMBOLS	SS32F	SS33F	SS34F	SS35F	SS36F	SS38F	SS310F	SS3150F	SS3200F	UNITS	
Maximum repetitive peak reverse voltage	V_{RRM}	20	30	40	50	60	80	100	150	200	VOLTS	
Maximum RMS voltage	V_{RMS}	14	21	28	35	42	56	70	105	140	VOLTS	
Maximum DC blocking voltage	V_{DC}	20	30	40	50	60	80	100	150	200	VOLTS	
Maximum average forward rectified current at T_L (see fig.1)	$I_{(AV)}$	3.0									Amp	
Peak forward surge current 8.3ms single half sine-wave superimposed on rated load (JEDEC Method)	I_{FSM}	80.0									Amps	
Maximum instantaneous forward voltage at 3.0A	V_F	0.55			0.70			0.85		0.95	Volts	
Maximum DC reverse current $T_A=25^\circ\text{C}$ at rated DC blocking voltage $T_A=100^\circ\text{C}$	I_R	0.5						0.2			mA	
		20.0				10		2.0				
Typical junction capacitance (NOTE 1)	C_J	500			300						pF	
Typical thermal resistance (NOTE 2)	$R_{\theta JA}$	55.0									$^\circ\text{C/W}$	
Operating junction temperature range	T_J	-50 to +125					-50 to +150					$^\circ\text{C}$
Storage temperature range	T_{STG}	-50 to +150										$^\circ\text{C}$

Note: 1. Measured at 1MHz and applied reverse voltage of 4.0V D.C.
 2. P.C.B. mounted with 0.2x0.2" (5.0x5.0mm) copper pad areas

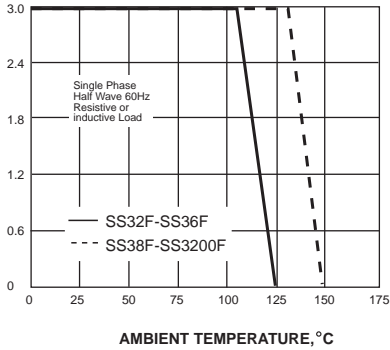


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RATINGS AND CHARACTERISTIC CURVES SS32F THRU SS3200F

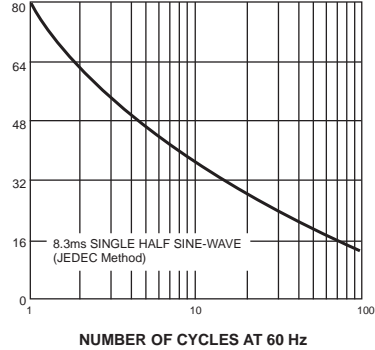
AVERAGE FORWARD RECTIFIED CURRENT, AMPERES

FIG. 1- FORWARD CURRENT DERATING CURVE



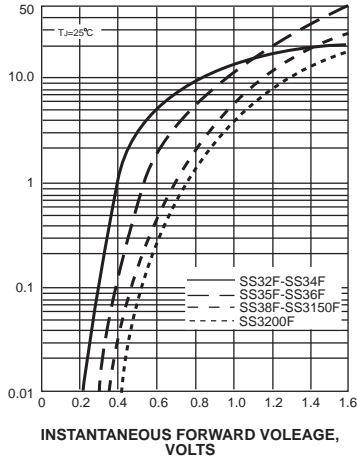
PEAK FORWARD SURGE CURRENT, AMPERES

FIG. 2-MAXIMUM NON-REPETITIVE PEAK FORWARD SURGE CURRENT



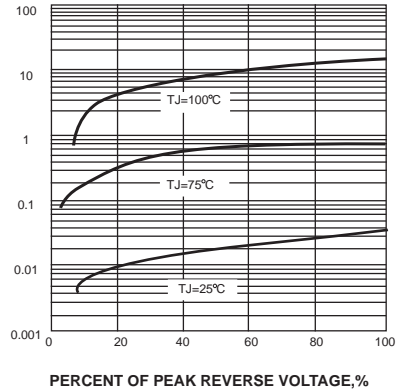
INSTANTANEOUS FORWARD CURRENT, AMPERES

FIG. 3-TYPICAL INSTANTANEOUS FORWARD CHARACTERISTICS



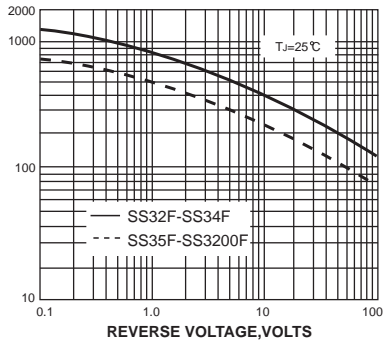
INSTANTANEOUS REVERSE CURRENT, MILLIAMPERES

FIG. 4-TYPICAL REVERSE CHARACTERISTICS



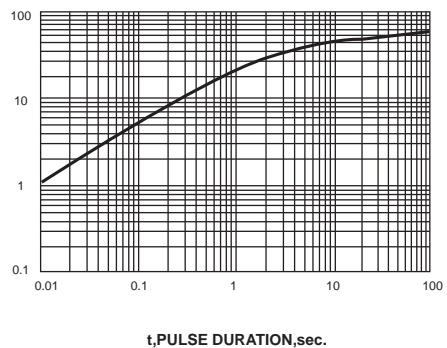
JUNCTION CAPACITANCE, pF

FIG. 5-TYPICAL JUNCTION CAPACITANCE



TRANSIENT THERMAL IMPEDANCE, °C/W

FIG. 6-TYPICAL TRANSIENT THERMAL IMPEDANCE



The cruve graph is for reference only, can't be the basis for judgment(曲线图仅供参考)!



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